

Attorney Docket. No. FUJI:294

Amendments to the Specification

Please amend the specification as follows:

Please replace paragraphs 0068 and 0069, with the following rewritten paragraph:

[0068] A CrB film 100 nm thick was deposited on a glass substrate. After patterning, the processes of drying (at 150°C) and UV treatment (at room temperature and at 150°C) were conducted to form a reflective electrode of CrB. Deposition of the CrB film was carried out by a DC sputtering method under room temperature using sputtering gas of argon supplying sputtering power of 300 W. ~~On the reflective electrode of CrB, an anode of IZO that was 125 nm thick was formed. Deposition of the anode of IZO was carried out by DC sputtering using a target of IZO (In₂O₃-10%ZnO) and argon as the sputtering gas.~~

[0069] The glass substrate with the reflective layer ~~and the anode~~ electrode of CrB formed thereon in the previous steps was moved to an evaporation apparatus. The vacuum chamber was evacuated to 1×10^{-5} Pa. Holding the vacuum, an organic EL layer, a buffer structure, and a cathode were sequentially formed. The organic EL layer was comprised of a hole injection layer, a hole transport layer, an organic light emissive layer, and an electron transport layer. The hole injection layer was formed by depositing copper phthalocyanine (CuPc) to a thickness of 20 nm. The hole transport layer was formed by depositing 4,4'-bis[N-(1-naphthyl)-N-phenylamino] biphenyl (α -NPD) to a thickness of 20 nm. The organic light emissive layer was formed by depositing 4,4'-bis(2,2'-diphenylvinyl) biphenyl (DPVBi) to a thickness of 40 nm. The electron transport layer was formed by depositing aluminum chelate (Alq₃) to a thickness of 20 nm.